

PLEASE AMEND THE CLAIMS - CLEAN COPY

21. A Salicide field effect transistor with improved borderless contact openings comprised of:

a semiconductor substrate doped with a first conductive type dopant and having device areas surrounded and electrically isolated by shallow trench field oxide areas;

a gate oxide layer on said device areas, and a conductively doped patterned polysilicon layer doped with a second conductive type dopant over said device areas for gate electrodes;

lightly doped source/drain areas with said second conductive type dopant in said device areas adjacent to said gate electrodes and insulating sidewall spacers on the sidewalls of said gate electrodes;

heavily doped first source/drain contact areas composed of said second conductive type dopant in said device areas adjacent to said insulating sidewall spacers;

a silicide layer on said gate electrodes and on said source/drain contact providing said Salicide field effect transistors;

a conformal barrier layer, and an interlevel dielectric layer on said Salicide field effect transistor;

25 borderless contact openings in said interlevel dielectric layer and said barrier layer to said source/drain areas and extending over said field oxide with unintentional over-etched field oxide regions at said field oxide-source/drain area interface;

DI could 30 a dopant composed of said second conductive type in said substrate under and adjacent to said over-etched field oxide regions in said borderless contact openings and providing said source/drain contact areas with a conformal continuous ion implanted doped region in said
 35 substrate surrounding said unintentional over-etched field oxide regions, and said ion implanted doped region is shallower than said source/drain contact areas.

REMARKS

Examiner A. Roman is thanked for a complete search and thorough Office Action. The Examiner is also thanked for pointing out that the contact-opening ion implant, which is carried out after etching the contact openings, is not recited in the claims.

During review of claim 21, two grammatical changes were made for clarity. On line 5 please insert the word --by-- after the word "isolated" and on line 13 please delete the word "an" after the word "and."